Amendments to th Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of claims:

Claim 1 (withdrawn): A method of producing an oxidation-protected electrode for a capacitive electrode structure, which comprises the following steps:

forming a metal oxide layer on a substrate;

applying an oxidation inhibiting layer, configured to be impervious to oxygen atoms, on the metal oxide layer; and

forming an electrode on the oxidation inhibiting layer.

Claim 2 (withdrawn): The method according to claim 1, wherein the step of forming the metal oxide layer comprises thermally oxidizing a deposited metal layer.

Claim 3 (withdrawn): The method according to claim 1, which comprises forming a metal barrier layer between the metal oxide layer and the substrate.

Claim 4 (withdrawn): The method according to claim 1, wherein the applying step comprises forming the oxidation inhibiting layer by chemical vapor phase deposition.

Claim 5 (currently amended): A capacitive electrode structure, comprising:

a semiconductor substrate including silicon;

a metal barrier layer disposed on said semiconductor substrate, said metal barrier layer being one of silicon oxide and silicon nitride;

a metal-oxide-layer ~~formed~~ disposed on said ~~semiconductor substrate~~ metal barrier layer, said metal-oxide-layer ~~containing molecules in the form of a metal-oxide-compound~~ being one of TiO_2, Ta_2O_5, and Al_2O_3;

an oxidation inhibiting layer disposed on said metal-oxide-layer, said oxidation inhibiting layer being one of titanium nitride and tungsten silicide; and

~~an electrode~~ a metal layer disposed on said oxidation inhibiting layer.

Claims 6-20 (cancelled).

Claim 21 (new): A capacitive electrode structure, comprising:

a semiconductor substrate including silicon;

a metal barrier layer disposed on said semiconductor substrate, said metal barrier layer being one of silicon oxide and silicon nitride;

a metal oxide layer disposed on said metal barrier layer, said metal oxide layer being one of TiO_2, Ta_2O_5, and Al_2O_3;

an oxidation inhibiting layer disposed on said metal oxide layer, said oxidation inhibiting layer being silicon nitride; and

a polysilicon layer disposed on said oxidation inhibiting layer.